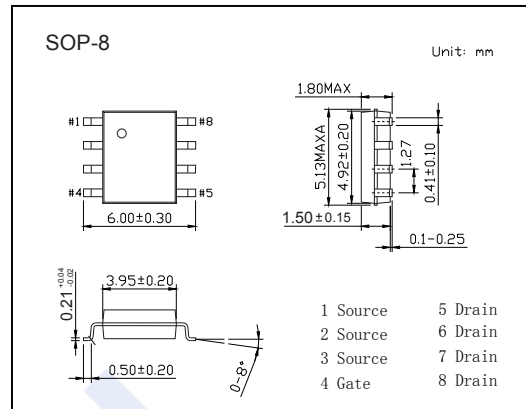
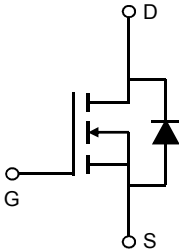


N-Channel MOSFET

AO4406A-HF (KO4406A-HF)

■ Features

- $V_{DS} (V) = 30V$
- $I_D = 13 A (V_{GS} = 10V)$
- $R_{DS(ON)} < 11.5m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 15.5m\Omega (V_{GS} = 4.5V)$
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V_{DS}	30	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current	I_D	$T_A=25^\circ C$	13	A
		$T_A=70^\circ C$	10.4	
Pulsed Drain Current	I_{DM}	100		
Avalanche Current	I_{AS}	22		
Avalanche energy	$L=0.1mH$	E_{AS}	24	mJ
Power Dissipation	P_D	$T_A=25^\circ C$	3.1	W
		$T_A=70^\circ C$	2	
Thermal Resistance.Junction- to-Ambient	R_{thJA}	$t \leq 10s$	40	$^\circ C/W$
		Steady-State	75	
Thermal Resistance.Junction- to-Lead	R_{thJL}	24		
Junction Temperature	T_J	150	$^\circ C$	
Storage Temperature Range	T_{stg}	-55 to 150		

N-Channel MOSFET

AO4406A-HF (KO4406A-HF)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μA, V _{GS} =0V	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μA
		V _{DS} =30V, V _{GS} =0V, T _J =55°C			5	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.5		2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =12A			11.5	mΩ
		V _{GS} =10V, I _D =12A, T _J =125°C			17	
		V _{GS} =4.5V, I _D =10A			15.5	
On State Drain Current	I _{D(ON)}	V _{GS} =10V, V _{DS} =5V	100			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =12A		45		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =15V, f=1MHz	610		910	pF
Output Capacitance	C _{oss}		88		160	
Reverse Transfer Capacitance	C _{rss}		40		100	
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.8		2.4	Ω
Total Gate Charge (10V)	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =12A	11		17	nC
Total Gate Charge (4.5V)			5		8	
Gate Source Charge	Q _{gs}		1.9		2.9	
Gate Drain Charge	Q _{gd}		1.8		4.2	
Turn-On DelayTime	t _{d(on)}		V _{GS} =10V, V _{DS} =15V, R _L =1.25Ω, R _{GEN} =3Ω		4.4	
Turn-On Rise Time	t _r			9		
Turn-Off DelayTime	t _{d(off)}			17		
Turn-Off Fall Time	t _f			6		
Body Diode Reverse Recovery Time	t _{rr}	I _F = 12A, di/dt= 500A/us	5.6		8	nC
Body Diode Reverse Recovery Charge	Q _{rr}		6.4		9.6	
Maximum Body-Diode Continuous Current	I _S				4	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V

Note : The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

■ Marking

Marking	4406A
	KC**** F

N-Channel MOSFET AO4406A-HF (KO4406A-HF)

■ Typical Characteristics

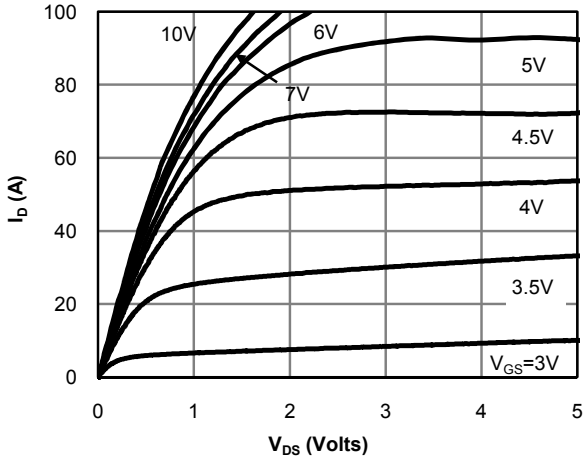


Fig 1: On-Region Characteristics (Note E)

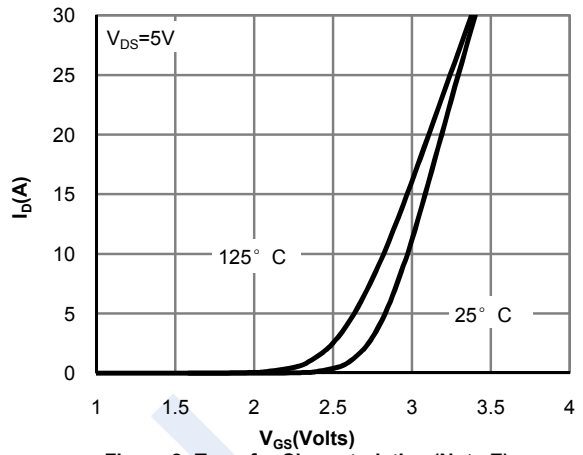


Figure 2: Transfer Characteristics (Note E)

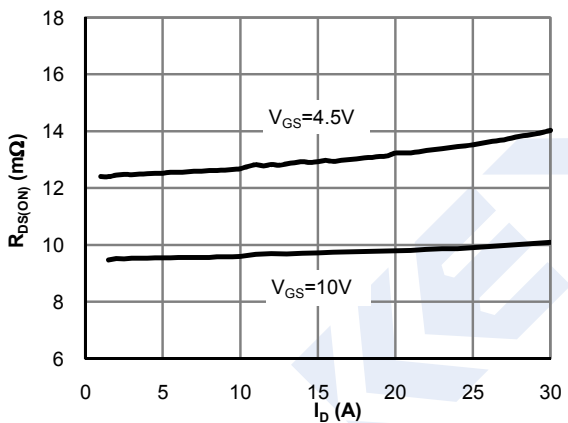


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

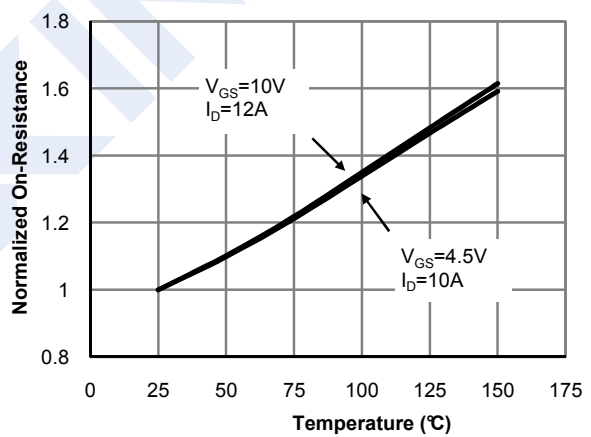


Figure 4: On-Resistance vs. Junction Temperature (Note E)

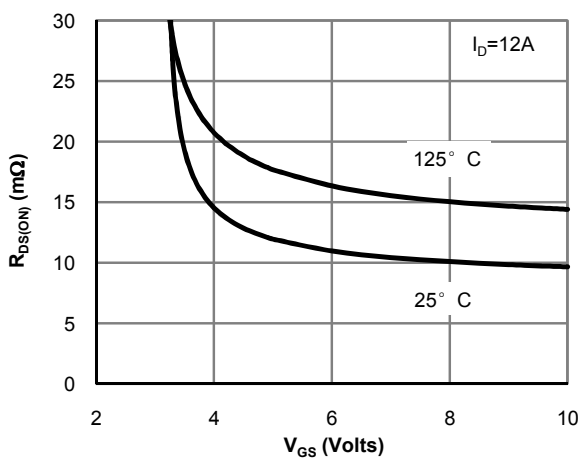


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

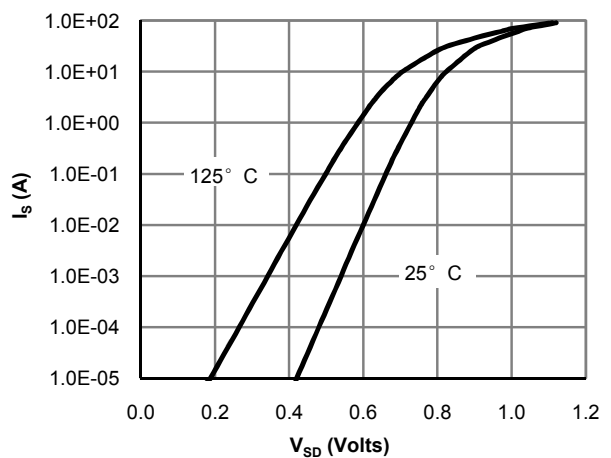


Figure 6: Body-Diode Characteristics (Note E)

N-Channel MOSFET AO4406A-HF (KO4406A-HF)

■ Typical Characteristics

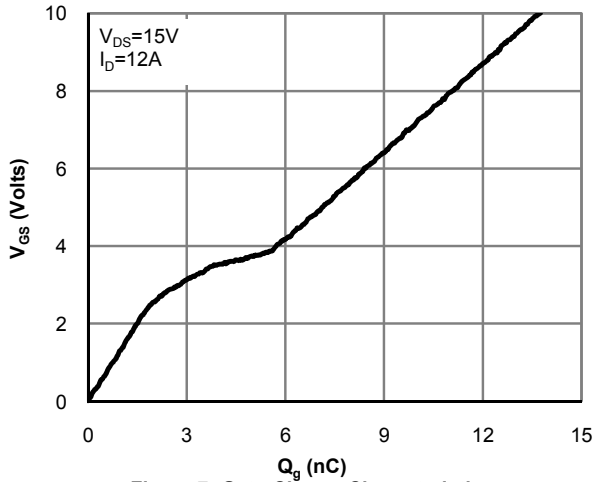


Figure 7: Gate-Charge Characteristics

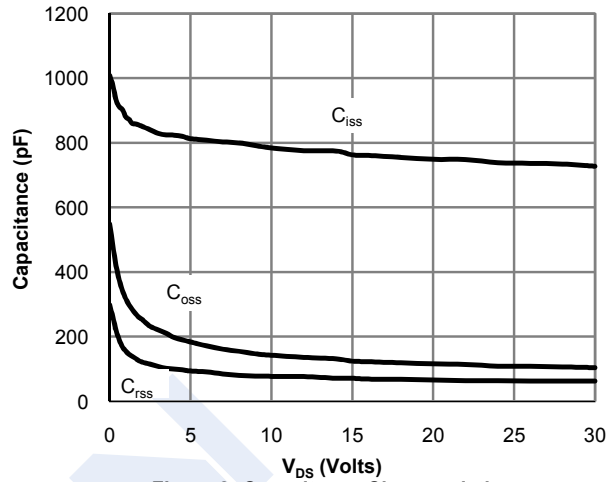


Figure 8: Capacitance Characteristics

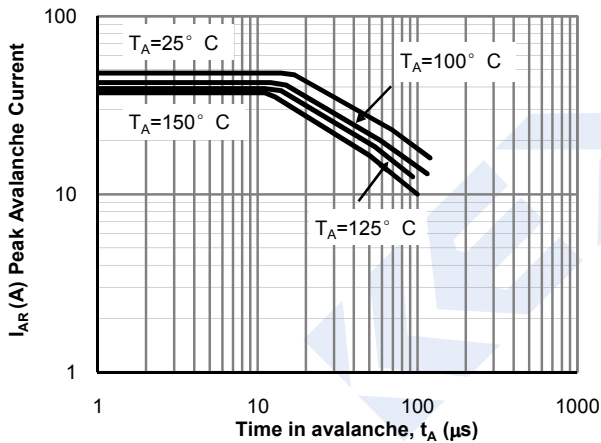


Figure 9: Single Pulse Avalanche capability (Note C)

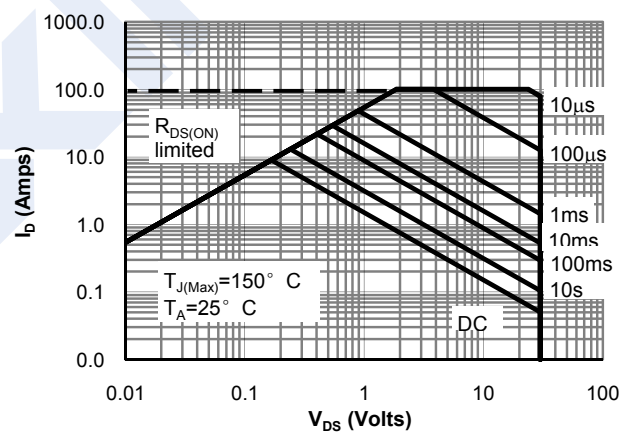


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

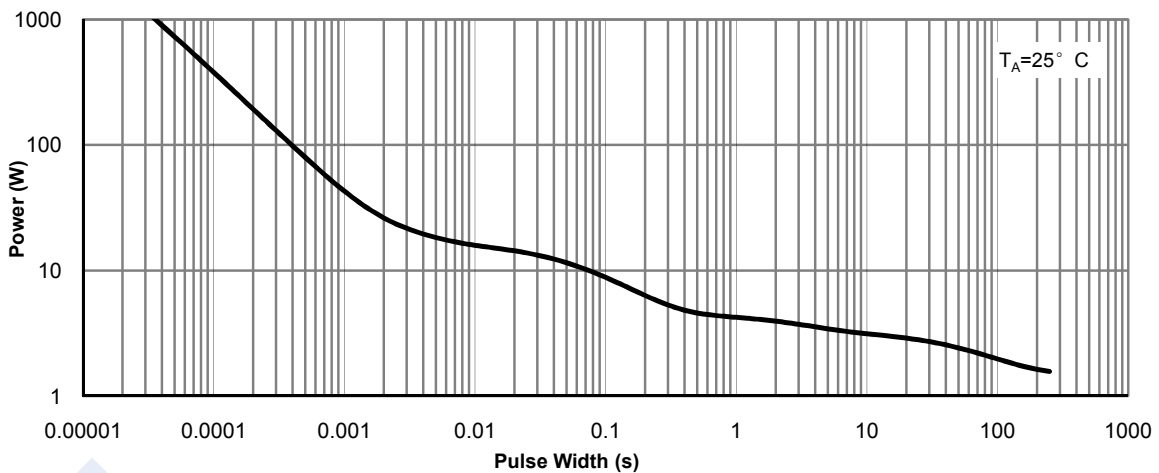


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

N-Channel MOSFET AO4406A-HF (KO4406A-HF)

■ Typical Characteristics

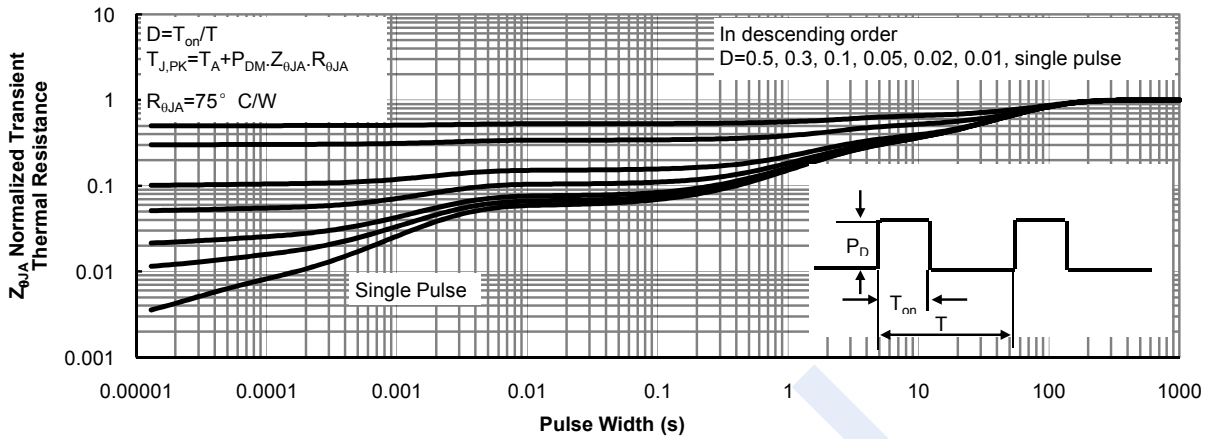


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)